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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100lgdfb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(11/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	Mounted	А	R5F100PFAFB#V0, R5F100PGAFB#V0, R5F100PHAFB#V0, R5F100PJAFB#V0, R5F100PKAFB#V0, R5F100PLAFB#V0 R5F100PFAFB#X0, R5F100PGAFB#X0, R5F100PHAFB#X0,
	min, 0.5 min pitch)			R5F100PJAFB#X0, R5F100PKAFB#X0, R5F100PLAFB#X0
			D	R5F100PFDFB#V0, R5F100PGDFB#V0, R5F100PHDFB#V0,
				R5F100PJDFB#V0, R5F100PKDFB#V0, R5F100PLDFB#V0
				R5F100PFDFB#X0, R5F100PGDFB#X0, R5F100PHDFB#X0,
				R5F100PJDFB#X0, R5F100PKDFB#X0, R5F100PLDFB#X0
			G	R5F100PFGFB#V0, R5F100PGGFB#V0, R5F100PHGFB#V0,
				R5F100PJGFB#V0
				R5F100PFGFB#X0, R5F100PGGFB#X0, R5F100PHGFB#X0,
				R5F100PJGFB#X0
		Not	Α	R5F101PFAFB#V0, R5F101PGAFB#V0, R5F101PHAFB#V0,
		mounted		R5F101PJAFB#V0, R5F101PKAFB#V0, R5F101PLAFB#V0
				R5F101PFAFB#X0, R5F101PGAFB#X0, R5F101PHAFB#X0,
				R5F101PJAFB#X0, R5F101PKAFB#X0, R5F101PLAFB#X0
			D	R5F101PFDFB#V0, R5F101PGDFB#V0, R5F101PHDFB#V0,
				R5F101PJDFB#V0, R5F101PKDFB#V0, R5F101PLDFB#V0
				R5F101PFDFB#X0, R5F101PGDFB#X0, R5F101PHDFB#X0,
				R5F101PJDFB#X0, R5F101PKDFB#X0, R5F101PLDFB#X0
	100-pin plastic	Mounted	Α	R5F100PFAFA#V0, R5F100PGAFA#V0, R5F100PHAFA#V0,
	LQFP (14 × 20 mm,			R5F100PJAFA#V0, R5F100PKAFA#V0, R5F100PLAFA#V0
	0.65 mm pitch)			R5F100PFAFA#X0, R5F100PGAFA#X0, R5F100PHAFA#X0,
				R5F100PJAFA#X0, R5F100PKAFA#X0, R5F100PLAFA#X0
			D	R5F100PFDFA#V0, R5F100PGDFA#V0, R5F100PHDFA#V0,
				R5F100PJDFA#V0, R5F100PKDFA#V0, R5F100PLDFA#V0
				R5F100PFDFA#X0, R5F100PGDFA#X0, R5F100PHDFA#X0,
				R5F100PJDFA#X0, R5F100PKDFA#X0, R5F100PLDFA#X0
			G	R5F100PFGFA#V0, R5F100PGGFA#V0, R5F100PHGFA#V0,
				R5F100PJGFA#V0
				R5F100PFGFA#X0, R5F100PGGFA#X0, R5F100PHGFA#X0,
				R5F100PJGFA#X0
		Not	Α	R5F101PFAFA#V0, R5F101PGAFA#V0, R5F101PHAFA#V0,
		mounted		R5F101PJAFA#V0, R5F101PKAFA#V0, R5F101PLAFA#V0
				R5F101PFAFA#X0, R5F101PGAFA#X0, R5F101PHAFA#X0,
				R5F101PJAFA#X0, R5F101PKAFA#X0, R5F101PLAFA#X0
			D	R5F101PFDFA#V0, R5F101PGDFA#V0, R5F101PHDFA#V0,
				R5F101PJDFA#V0, R5F101PKDFA#V0, R5F101PLDFA#V0
				R5F101PFDFA#X0, R5F101PGDFA#X0, R5F101PHDFA#X0,
				R5F101PJDFA#X0, R5F101PKDFA#X0, R5F101PLDFA#X0

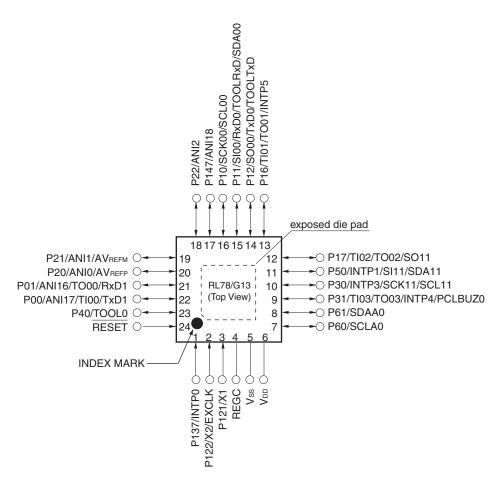
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



### 1.3.2 24-pin products

• 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)



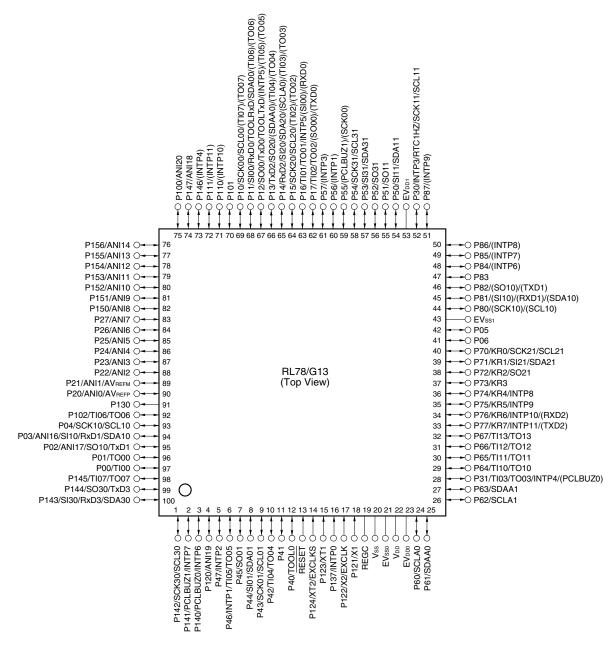
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. It is recommended to connect an exposed die pad to  $V_{\mbox{\scriptsize ss}}.$ 

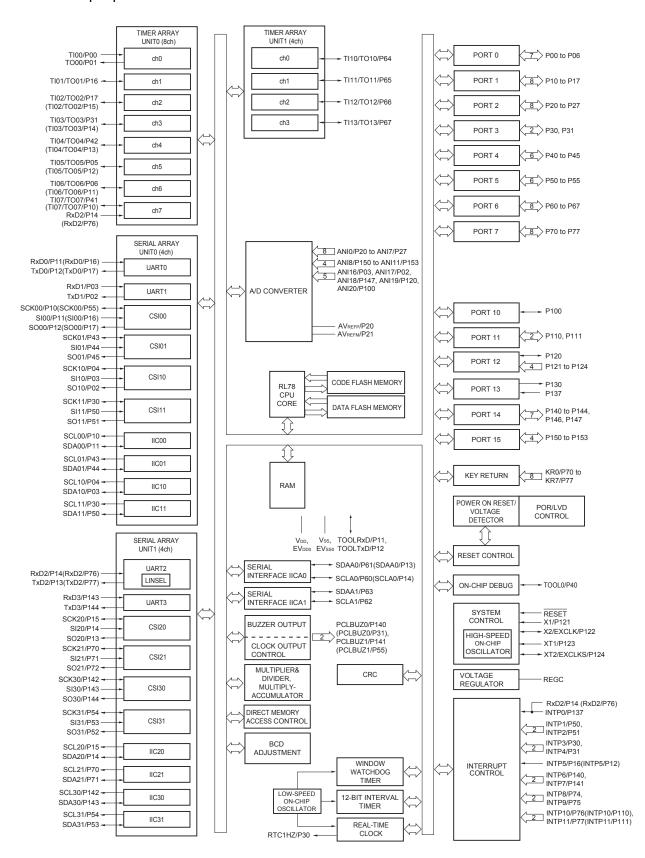
### 1.3.13 100-pin products

• 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)



- Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.
  - 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
  - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
  - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V<sub>DD</sub>, EV<sub>DDO</sub> and EV<sub>DD1</sub> pins and connect the Vss, EV<sub>SS0</sub> and EV<sub>SS1</sub> pins to separate ground lines.
  - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

### 1.5.12 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

**3.** The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

4. When setting to PIOR = 1

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Iter	m	20-	nin	24-	nin	25-	nin	30-	pin	32	-pin	36	pin
itoi											İ		İ
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzze	er output	-	=		1		1		2		2		2
				88 kHz, 9 n clock: fr				ИНz, 5 М	Hz, 10 N	МНz			
8/10-bit resolution	A/D converter	6 channels 6 channels 6 channels 8 channels 8 channels 8 channels											
Serial interface		[20-pin, 24-pin, 25-pin products]											
		CSI: 1 channel/simplified l <sup>2</sup> C: 1 channel/UART: 1 channel											
		• CSI:	1 chann	el/simplif	ied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanr	nel				
		[30-pin,	32-pin <sub> </sub>	products]	]								
		• CSI:	1 chann	el/simplif el/simplif	ied I <sup>2</sup> C:	1 channe	el/UART	: 1 chanr	nel				
				el/simplif	fied I <sup>2</sup> C:	1 channe	el/UART	(UART s	supportir	ng LIN-b	us): 1 ch	nannel	
		[36-pin											
		1		el/simplif el/simplif									
1				els/simpl						rting LIN	-bus): 1	channel	
ſ	I <sup>2</sup> C bus	-	- 1 channel 1 channel 1 channel 1 channel										
Multiplier and divide accumulator	er/multiply-	<ul> <li>16 bits × 16 bits = 32 bits (Unsigned or signed)</li> <li>32 bits ÷ 32 bits = 32 bits (Unsigned)</li> <li>16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)</li> </ul>											
DMA controller		2 channels											
Vectored interrupt	Internal	2	3	2	24	2	<u>!</u> 4	2	27	2	27	2	27
sources	External	;	3	ļ	5		5		6		6		6
Key interrupt													
Reset													
		<ul><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li></ul>	nal reset nal reset nal reset nal reset nal reset	SET pin by watch by power by volta by illega by RAM by illega	er-on-res ge detec al instruc parity e	et ctor tion exec rror		e					
Power-on-reset circ	puit	<ul><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Powe</li></ul>	nal reset nal reset nal reset nal reset nal reset er-on-res	by watch by power by volta by illega by RAM by illega	er-on-res ge detect al instruct parity e al-memod	et stor stor tion exec rror ry access		0					
Power-on-reset circ	cuit	<ul><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Interr</li><li>Powe</li></ul>	nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser er-down-	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detectal instruction parity et al-memorial.51 V (Tours) (	et stor stor tion exec rror ry access	s 14 stage	es)					
		Interr Interr Interr Interr Interr Interr Interr Powe	nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser-down- g edge: g edge	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detectal instruction parity et al-memorial.51 V (Tours) (	et ctor tion exec rror ry access YP.) YP.)	s 14 stage	es)					
Voltage detector	ction	Interresident In	nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser-down- g edge: g edge d	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detect al instruct parity e al-memon .51 V (T .50 V (T .67 V to	set stor rich execution ex	s 14 stage	es)					
Voltage detector  On-chip debug fund	ction	<ul> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Powe</li> <li>Powe</li> <li>Rising</li> <li>Fallin</li> <li>Provide</li> </ul>	nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser down- g edge: g edge d	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detect al instruct parity e al-memon .51 V (T .50 V (T .67 V to .63 V to	set stor return execution exec	s 14 stage	es)					
Voltage detector  On-chip debug fund	ction	<ul> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Interr</li> <li>Powe</li> <li>Powe</li> <li>Rising</li> <li>Fallin</li> <li>Provide</li> <li>V<sub>DD</sub> = 1</li> <li>V<sub>DD</sub> = 2.</li> </ul>	nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser er-down- g edge g edge d .6 to 5.5	by watch by power by volta by illegate by RAM by illegate by illeg	er-on-res ge detect al instruct parity e al-memor .51 V (T .50 V (T .63 V to .63 V to	set stor rich execution ex	s 14 stage 14 stage	es)	applica	tions)			

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

#### 2.3 DC Characteristics

### 2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$ 

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high <sup>Note 1</sup>	Іонт	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-10.0 Note 2	mA
		P40 to P47, P102 to P106, P120,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-55.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			-10.0	mA
		P125 to P127, P130, P140 to P145 (When duty $\leq 70\%$ Note 3)	$1.8~V \leq EV_{DD0} < 2.7~V$			-5.0	mA
			$1.6~V \leq EV_{DD0} < 1.8~V$			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80				-80.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
		to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	$1.8~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		(When duty ≤ 70% Note 3)	$1.6~V \leq EV_{DD0} < 1.8~V$			-5.0	mA
		Total of all pins (When duty $\leq 70\%$ Note 3)	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-135.0 Note 4	mA
	10н2	Per pin for P20 to P27, P150 to P156	$1.6~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty $\leq 70\%$ Note 3)	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV<sub>DD0</sub>, EV<sub>DD1</sub>, V<sub>DD</sub> pins to an output pin.
  - 2. However, do not exceed the total current value.
  - 3. Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins =  $(IOH \times 0.7)/(n \times 0.01)$ 

<Example> Where n = 80% and loh = -10.0 mA

Total output current of pins =  $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

**4.** The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V) (5/5)

Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVDDO				1	μΑ
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	$V_{I} = V_{DD}$				1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	lut1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVsso	Vi = EVsso			-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μΑ
	Ішз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	R∪	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vı = EVsso	, In input port	10	20	100	kΩ

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
  - 3. When high-speed system clock and subsystem clock are stopped.
  - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
  - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 32 MHz

 $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz$  to 16~MHz

LS (low-speed main) mode: 1.8 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
  - 2. fih: High-speed on-chip oscillator clock frequency
  - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - 4. Except subsystem clock operation, temperature condition of the TYP. value is T<sub>A</sub> = 25°C

#### (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ 

Parameter	Symbol		Conditions		speed	high- I main) ode	LS (low-speed main) Mode		LV (low- voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fack Note 4		5.3		1.3		0.6	Mbps
			$1.8 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps

**Notes 1.** Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with EVDD0≥Vb.
- 3. The following conditions are required for low voltage interface when  $E_{VDDO} < V_{DD}$ .

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 2.6 \text{ Mbps}$  $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$ 

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V)

16 MHz (2.4 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpd tolerance (When 20- to 52-pin products)/EVpd tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For ViH and ViL, see the DC characteristics with TTL input buffer selected.

**Remarks 1.**  $V_b[V]$ : Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmcκ: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

### (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ 

Parameter	Symbol	C, 1.0 V S E V	Conditions			high-	LS (	low-		low- age Mode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			Note 1		Note 1		Note 1	bps
				Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			Note 3		Note 3		Note 3	bps
			2.3 V ≤ Vb ≤ 2.7 V	Theoretical value of the maximum transfer rate  Cb = 50 pF, Rb =		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
				$2.7 \text{ k}\Omega, V_b = 2.3$							
			$1.8 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$			Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
				Theoretical value of the maximum transfer rate		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$							

**Notes 1.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V  $\leq$  EV  $_{DD0} \leq$  5.5 V and 2.7 V  $\leq$  V  $_{b} \leq$  4.0 V

Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- \* This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.



## (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	, 0	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸı	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	81		479		479		ns
		$C_b = 30$ pF, $R_b = 1.4$ k $\Omega$							
			177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\label{eq:local_local_local_local_local} \begin{split} 1.8 \ V & \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V & \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{split}$	479		479		479		ns
		$C_b = 30$ pF, $R_b = 5.5$ k $\Omega$							
SIp hold time (from SCKp↑) Note 1	<b>t</b> KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30$ pF, $R_b = 5.5$ k $\Omega$							
Delay time from SCKp↓ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		483		483		483	ns
		$C_b = 30$ pF, $R_b = 5.5$ k $\Omega$							

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with  $EV_{DD0} \ge V_b$ .

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

### (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$  (2/2)

Parameter	Symbol	Conditions	HS (	high- main) ode	LS (low		,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	tкн2, tкL2	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, $ $ 2.7 \ V \leq V_b \leq 4.0 \ V $	tксу2/2 - 12		tксү2/2 - 50		txcy2/2 - 50		ns
		$ 2.7 \ V \le EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \le V_b \le 2.7 \ V $	tксу2/2 - 18		tксү2/2 - 50		txcy2/2 - 50		ns
		$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{aligned}$	tkcy2/2 - 50		tксү2/2 - 50		tkcy2/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	tsık2	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V \end{aligned}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{aligned}$	1/fмск + 30		1/fмск + 30		1/fмcк + 30		ns
SIp hold time (from SCKp <sup>↑</sup> ) Note 4	tksi2		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 5	tkso2	$ 4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0 $ $V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega $		2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \\ \text{V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \ \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $		2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$\begin{split} &1.8 \; V \leq \text{EV}_{\text{DD0}} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 30 \; p\text{F}, \; R_b = 5.5 \; k\Omega \end{split}$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- 2. Use it with  $EV_{DD0} \ge V_b$ .
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **5.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V<sub>DD</sub> tolerance (for the 20- to 52-pin products)/EV<sub>DD</sub> tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V<sub>IH</sub> and V<sub>IL</sub>, see the DC characteristics with TTL input buffer selected.

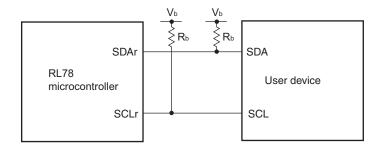
(Remarks are listed on the next page.)

### (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode) (1/2)

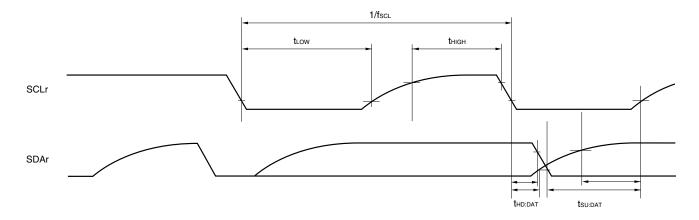
(Ta = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	` `	h-speed Mode	`	v-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		400 Note 1		300 Note 1		300 Note 1	kHz
		eq:second-seco		400 Note 1		300 Note 1		300 ote 1	kHz
		$\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	475		1550		1550		ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	475		1550		1550		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1150		1550		1550		ns
		$\label{eq:section} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1150		1550		1550		ns
		$\begin{split} &1.8~V \leq EV_{DD0} < 3.3~V,\\ &1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}},\\ &C_b = 100~pF,~R_b = 5.5~k\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tніgн	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	245		610		610		ns
		$\label{eq:section} \begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	200		610		610		ns
		$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned}$	675		610		610		ns
		$\begin{split} 2.7 \ V &\leq EV_{DDO} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	600		610		610		ns
		$\begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	610		610		610		ns

### Simplified I<sup>2</sup>C mode connection diagram (during communication at different potential)



### Simplified I<sup>2</sup>C mode serial transfer timing (during communication at different potential)



- **Remarks 1.**  $R_b[\Omega]$ :Communication line (SDAr, SCLr) pull-up resistance,  $C_b[F]$ : Communication line (SDAr, SCLr) load capacitance,  $V_b[V]$ : Communication line voltage
  - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency
    (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
    n: Channel number (mn = 00, 01, 02, 10, 12, 13)

# (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (Ta = -40 to $+105^{\circ}$ C, 2.4 V $\leq$ EV<sub>DD0</sub> = EV<sub>DD1</sub> $\leq$ V<sub>DD</sub> $\leq$ 5.5 V, Vss = EV<sub>SS0</sub> = EV<sub>SS1</sub> = 0 V) (2/2)

Parameter						MIN.	TYP.	MAX.	Unit
Supply	I <sub>DD2</sub>	HALT	HS (high-	fin = 32 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.62	3.40	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V <sub>DD</sub> = 3.0 V		0.62	3.40	mA
			mode	fih = 24 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.50	2.70	mA
					V <sub>DD</sub> = 3.0 V		0.50	2.70	mA
				fih = 16 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.44	1.90	mA
					V <sub>DD</sub> = 3.0 V		0.44	1.90	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
			speed main) mode Note 7	V <sub>DD</sub> = 5.0 V	Resonator connection		0.48	2.20	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	2.10	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.48	2.20	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		0.21	1.10	mA
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.28	1.20	mA
				f <sub>MX</sub> = 10 MHz <sup>Note 3</sup> ,	Square wave input		0.21	1.10	mA
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.28	1.20	mA
			Subsystem clock operation	fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.28	0.61	μA
				T <sub>A</sub> = -40°C	Resonator connection		0.47	0.80	μА
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.34	0.61	μΑ
				T <sub>A</sub> = +25°C	Resonator connection		0.53	0.80	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.41	2.30	μA
				T <sub>A</sub> = +50°C Resonator connection			0.60	2.49	μΑ
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		0.64	4.03	μA
				T <sub>A</sub> = +70°C	Resonator connection		0.83	4.22	μА
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		1.09	8.04	μΑ
				T <sub>A</sub> = +85°C	Resonator connection		1.28	8.23	μА
				fsub = 32.768 kHz <sup>Note 5</sup>	Square wave input		5.50	41.00	μΑ
				T <sub>A</sub> = +105°C	Resonator connection		5.50	41.00	μА
	IDD3 <sup>Note 6</sup>	STOP	T <sub>A</sub> = -40°C				0.19	0.52	μΑ
		mode <sup>Note 8</sup>	T <sub>A</sub> = +25°C				0.25	0.52	μΑ
			T <sub>A</sub> = +50°C				0.32	2.21	μΑ
			$T_A = +70^{\circ}C$ $T_A = +85^{\circ}C$				0.55	3.94	μΑ
							1.00	7.95	μΑ
			T <sub>A</sub> = +105°C	: 			5.00	40.00	$\mu$ A

(Notes and Remarks are listed on the next page.)

### (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified $I^2C$ mode) (1/2) (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		400 Note 1	kHz
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$		100 Note 1	kHz
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$		100 Note 1	kHz
		$\begin{split} &2.4 \; V \leq \text{EV}_{\text{DDO}} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V, \\ &C_b = 100 \; p\text{F}, \; R_b = 5.5 \; k\Omega \end{split}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLow	$\begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1200		ns
		$\begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1200		ns
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	4600		ns
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	4600		ns
		$\begin{split} 2.4 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V, \\ C_b &= 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	4650		ns
Hold time when SCLr = "H"	tніgн	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	620		ns
		$\begin{aligned} 2.7 & \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned}$	500		ns
		$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned}$	2700		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	2400		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$	1830		ns

( ${f Notes}$  and  ${f Caution}$  are listed on the next page, and  ${f Remarks}$  are listed on the page after the next page.)

### 4.10 52-pin Products

R5F100JCAFA, R5F100JDAFA, R5F100JEAFA, R5F100JFAFA, R5F100JGAFA, R5F100JHAFA, R5F100JJAFA, R5F100JKAFA, R5F100JLAFA

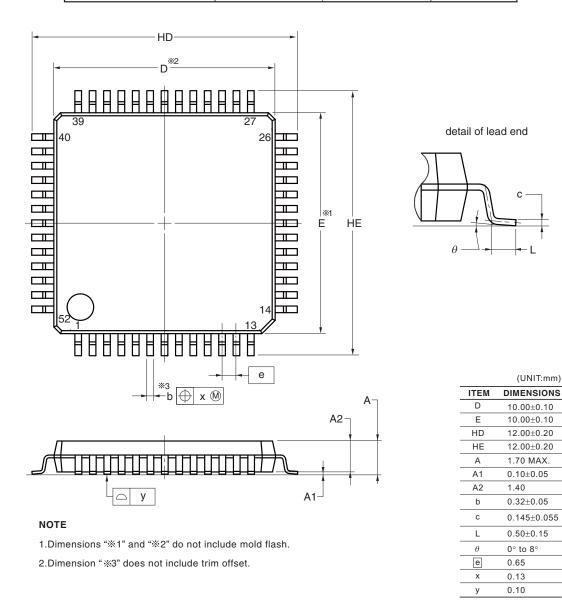
R5F101JCAFA, R5F101JDAFA, R5F101JEAFA, R5F101JFAFA, R5F101JJAFA, R5F101JJAFA, R5F101JJAFA, R5F101JAFA, R5F101JKAFA, R5F101JLAFA

R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JDFA, R5F100JPA, R R5F100JKDFA, R5F100JLDFA

R5F101JCDFA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JDFA, R5 R5F101JKDFA, R5F101JLDFA

R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



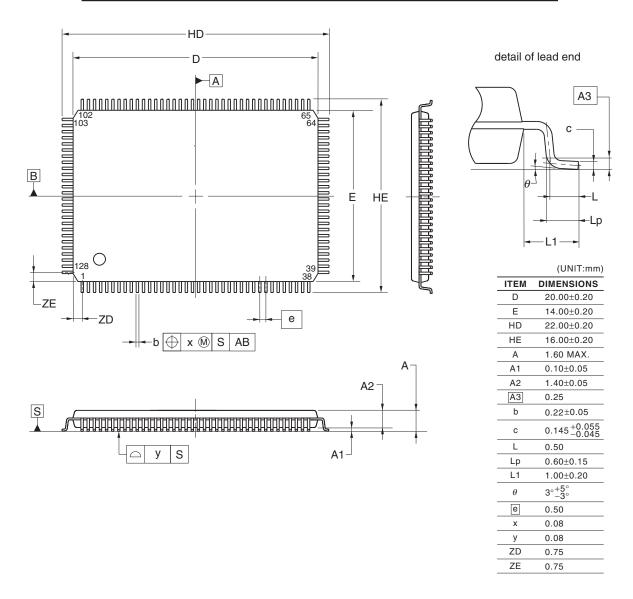
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(UNIT:mm)

### 4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



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			Description	
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3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics	
		118	Modification of table and note in 2.6.3 POR circuit characteristics	
		119	Modification of table in 2.6.4 LVD circuit characteristics	
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode	
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics	
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes	
		123	Modification of caution 1 and description	
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T <sub>A</sub> = 25°C)	
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics	
		126	Modification of table in 3.2.2 On-chip oscillator characteristics	
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)	
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)	
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)	
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)	
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)	
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)	
		140	Modification of (3) Peripheral Functions (Common to all products)	
		142	Modification of table in 3.4 AC Characteristics	
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation	
		143	Modification of figure of AC Timing Test Points	
		143	Modification of figure of External System Clock Timing	
		145	Modification of figure of AC Timing Test Points	
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)	
		146	Modification of description in (2) During communication at same potential (CSI mode)	
		147	Modification of description in (3) During communication at same potential (CSI mode)	
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I <sup>2</sup> C mode)	
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)	
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)	
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)	
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)	
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)	
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)	

			Description	
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3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I <sup>2</sup> C mode) (1/2)	
			Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I <sup>2</sup> C mode) (2/2)	
		166	Modification of table in 3.5.2 Serial interface IICA	
			Modification of IICA serial transfer timing	
		167	Addition of table in 3.6.1 A/D converter characteristics	
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)	
		169	Modification of description in 3.6.1 (2)	
		170	Modification of description and note 3 in 3.6.1 (3)	
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)	
			Modification of table and note in 3.6.3 POR circuit characteristics	
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode	
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics	
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)	
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes	
3.10	Nov 15, 2013	123	Caution 4 added.	
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.	
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 $\times$ 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products	
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]	
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]	
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]	
			ACK corrected to ACK	
			ACK corrected to ACK	

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